



IRFB4127PBF Information

Part Number IRFB4127PBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 200V 76A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com

E-mail: salesdept@heisener.com



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IRFB4127PBF Specifications

Manufacturer Part NumberIRFB4127PBFManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C76A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250µAGate Charge (Qg) (Max) @ Vgs150nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5380pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)375W (Tc)Rds On (Max) @ Id, Vgs20 mOhm @ 44A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3Report errors?		
Category Discrete Semiconductor Products Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 76A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 150nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5380pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 375W (Tc) Rds On (Max) @ Id, Vgs 20 mOhm @ 44A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer Part Number	IRFB4127PBF
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SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C76A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs150nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5380pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)375W (Tc)Rds On (Max) @ Id, Vgs20 mOhm @ 44A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C76A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs150nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5380pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)375W (Tc)Rds On (Max) @ Id, Vgs20 mOhm @ 44A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C76A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs150nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5380pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)375W (Tc)Rds On (Max) @ Id, Vgs20 mOhm @ 44A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	HEXFET?
Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C76A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs150nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5380pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)375W (Tc)Rds On (Max) @ Id, Vgs20 mOhm @ 44A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 150nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5380pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 20 mOhm @ 44A, 10V Operating Temperature Supplier Device Package TO-220AB Package / Case 76A (Tc) 76A (Tc)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sty @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB Package / Case	Drain to Source Voltage (Vdss)	200V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 5V @ 250μA 150nC @ 10V 15380pF @ 50V ±20V	Current - Continuous Drain (Id) @ 25°C	76A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 5380pF @ 50V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 20 mOhm @ 44A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 20 mOhm @ 44A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)375W (Tc)Rds On (Max) @ Id, Vgs20 mOhm @ 44A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	150nC @ 10V
FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 20 mOhm @ 44A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	5380pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 20 mOhm @ 44A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs20 mOhm @ 44A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	375W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	20 mOhm @ 44A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IRFB4127PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFB4127PBF Payment Methods





















IRFB4127PBF Shipping Methods













If you have any question about IRFB4127PBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com